

**30V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT89 PACKAGE**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	$I_D$ max $T_A = 25^\circ\text{C}$ (Note 5)
30V	120m $\Omega$ @ $V_{GS} = 10\text{V}$	3.3A
	180m $\Omega$ @ $V_{GS} = 4.5\text{V}$	2.7A

**Features and Benefits**

- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- **Lead Free/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

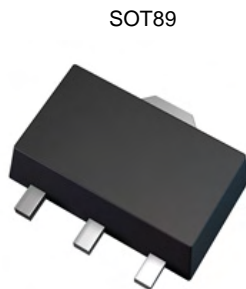
**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

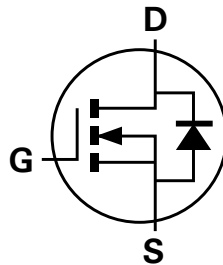
- DC-DC Converters
- Power Management functions
- Motor control

**Mechanical Data**

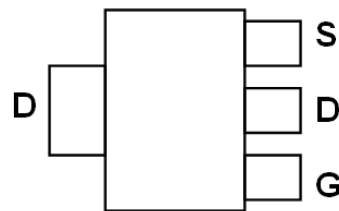
- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (approximate)



Top View



Device symbol



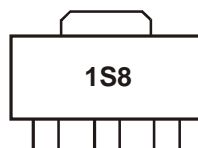
Pin-out Top

**Ordering Information** (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN3A01ZTA	1S8	7	12	1,000

- Notes:
1. No purposefully added lead.
  2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>
  3. For packaging details, go to our website at <http://www.diodes.com>

**Marking Information**



1S8 = Product type Marking Code

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current	Steady State	@ V <sub>GS</sub> = 10V ; T <sub>A</sub> = 25°C (Note 5)	3.3	A
		@ V <sub>GS</sub> = 10V ; T <sub>A</sub> = 75°C (Note 5)	2.7	
		@ V <sub>GS</sub> = 10V ; T <sub>A</sub> = 75°C (Note 4)	2.2	
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	20	A
Continuous Source Current (Body Diode) (Note 5)		I <sub>S</sub>	3.3	A
Pulsed Source Current (Body Diode) (Note 6)		I <sub>SM</sub>	20	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P <sub>D</sub>	0.97	W
	(Note 5)		2.12	W
	(Note 4)		129	°C/W
Thermal Resistance, Junction to Ambient	(Note 4)	R <sub>θJA</sub>	59	°C/W
	(Note 5)			
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes: 4. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout  
 5. Device mounted on 25mm X 25mm FR-4 substrate PC board with 2oz copper  
 6. Single pulse rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300us – pulse width limited by maximum junction temperature.

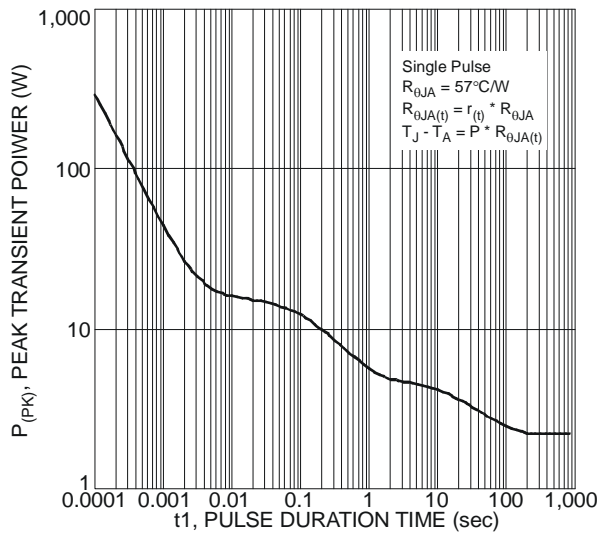


Fig. 1 Single Pulse Maximum Power Dissipation

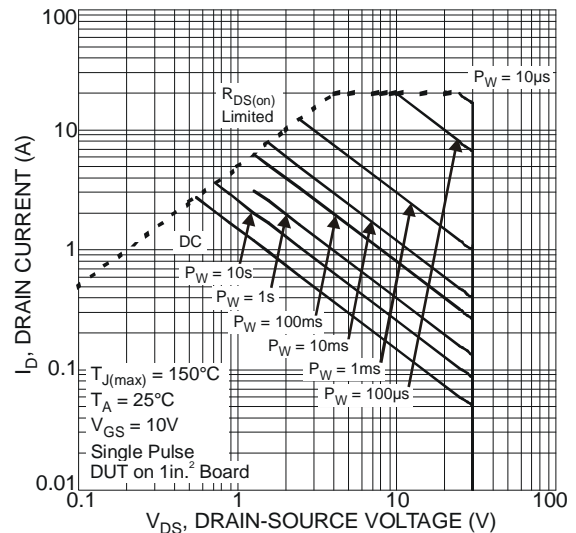


Fig. 2 SOA, Safe Operation Area

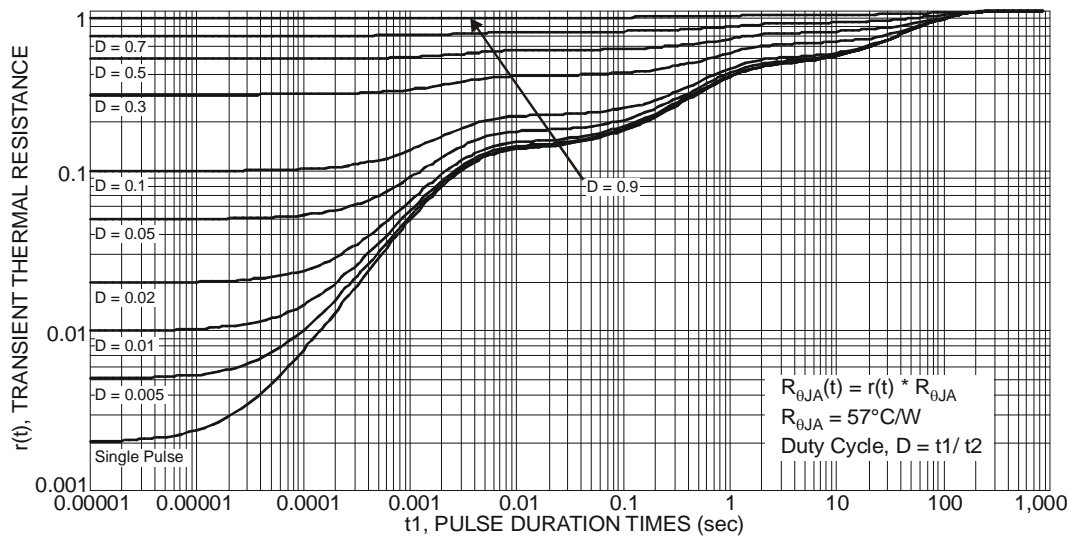


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	0.5	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	-	-	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>	-	0.106	120	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.5A
			-	180		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A
Forward Transconductance (Note 7 & 9)	g <sub>FS</sub>	-	3.5	-	S	V <sub>DS</sub> = 4.5V, I <sub>D</sub> = 2.5A
Diodes Forward Voltage (Note 7)	V <sub>SD</sub>	-	0.85	0.95	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 1.7A, V <sub>GS</sub> = 0V
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance (Note 8 & 9)	C <sub>iss</sub>	-	186	-	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance (Note 8 & 9)	C <sub>oss</sub>	-	48	-	pF	
Reverse Transfer Capacitance (Note 8 & 9)	C <sub>rss</sub>	-	29	-	pF	
Gate Charge (Note 8 & 9)	Q <sub>g</sub>	-	2.6	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.5A
Total Gate Charge (Note 8 & 9)	Q <sub>g</sub>	-	5.0	-	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.5A
Gate-Source Charge (Note 8 & 9)	Q <sub>gs</sub>	-	0.8	-	nC	
Gate-Drain Charge (Note 8 & 9)	Q <sub>gd</sub>	-	1.2	-	nC	
Reverse Recovery Time (Note 9)	t <sub>rr</sub>		17.7		ns	T <sub>J</sub> = 25°C, I <sub>S</sub> = 2.5A, di/dt = 100A/μs
Reverse Recovery Charge (Note 9)	Q <sub>rr</sub>		13.0		nC	
Turn-On Delay Time (Note 8 & 9)	t <sub>D(on)</sub>	-	2.6	-	ns	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 15V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 2.5A
Turn-On Rise Time (Note 8 & 9)	t <sub>r</sub>	-	4.1	-	ns	
Turn-Off Delay Time (Note 8 & 9)	t <sub>D(off)</sub>	-	13.5	-	ns	
Turn-Off Fall Time (Note 8 & 9)	t <sub>f</sub>	-	3.6	-	ns	

Notes: 7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.  
8. Switching characteristics are independent of operating junction temperature.  
9. For design aid only, not subject to production testing.

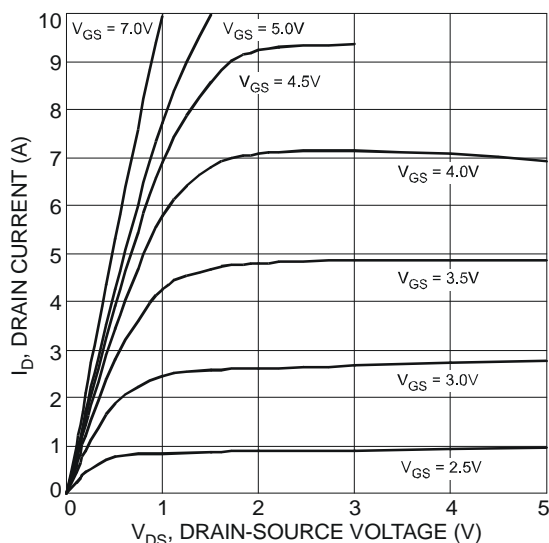


Fig. 4 Typical Output Characteristic, T<sub>A</sub> = 25°C

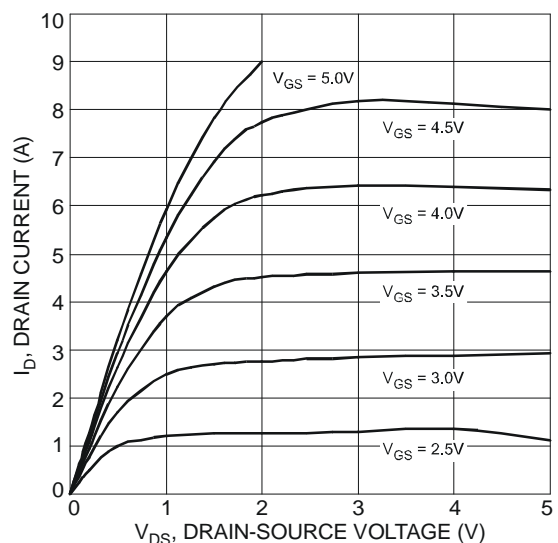


Fig. 5 Typical Output Characteristic, T<sub>A</sub> = 150°C

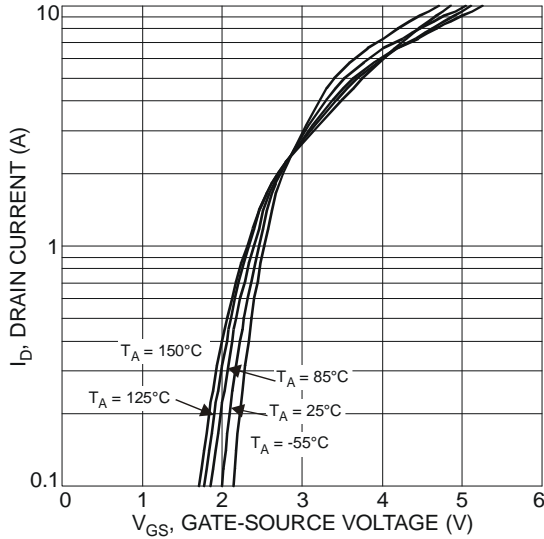


Fig. 6 Typical Transfer Characteristics

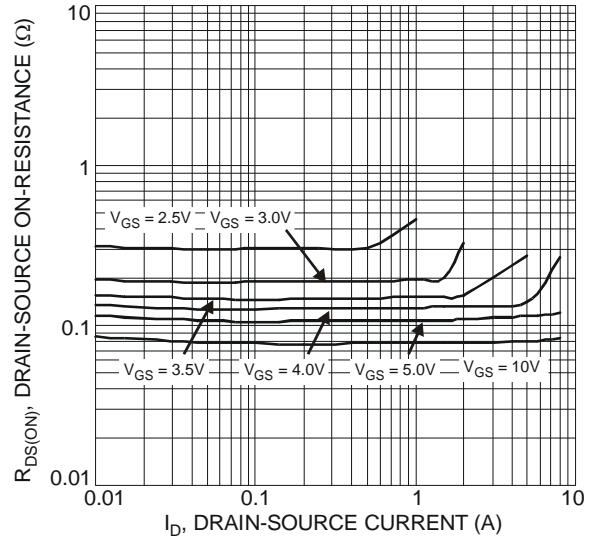


Fig. 7 Typical On-Resistance vs. Drain Current and Gate Voltage

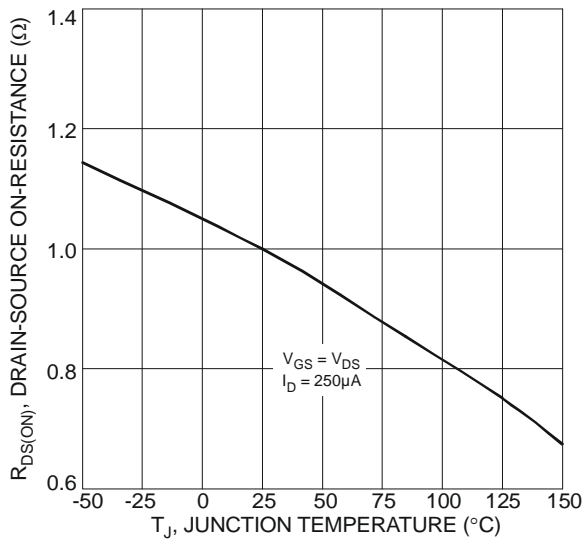


Fig. 8 On-Resistance Variation with Temperature

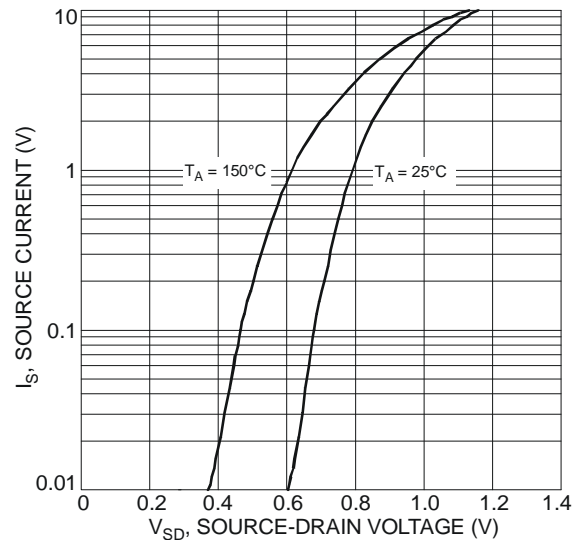


Fig. 9 Diode Forward Voltage vs. Current

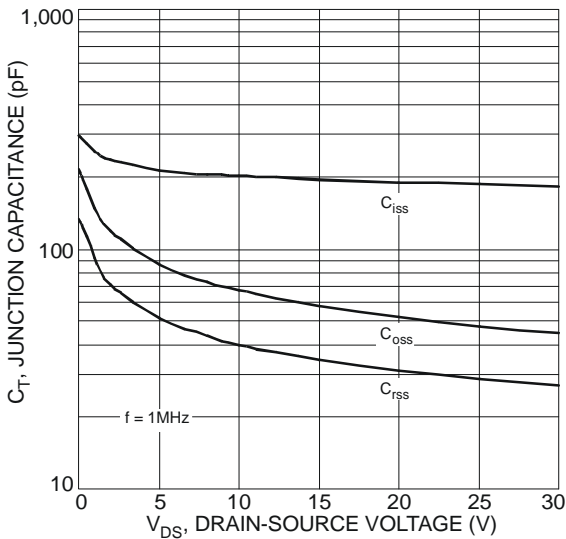


Fig. 10 Typical Junction Capacitance

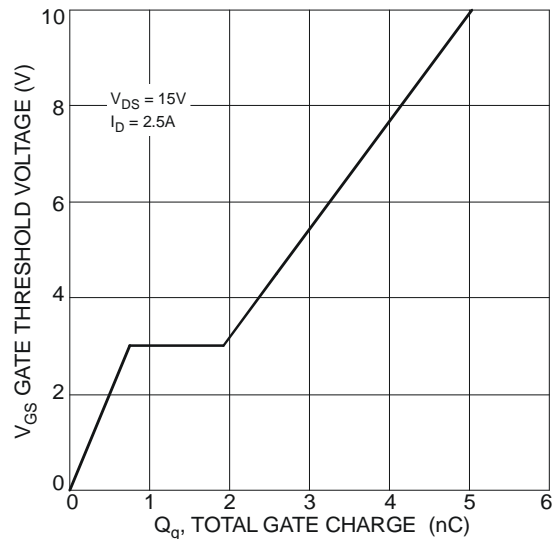
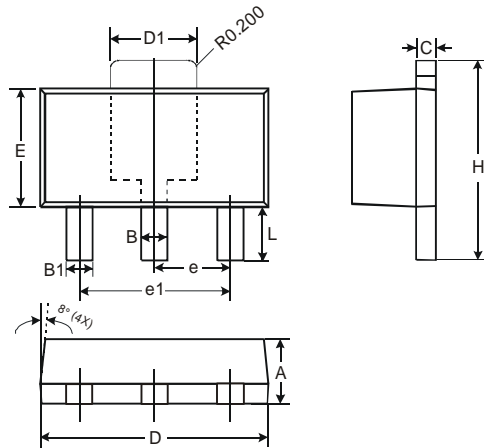


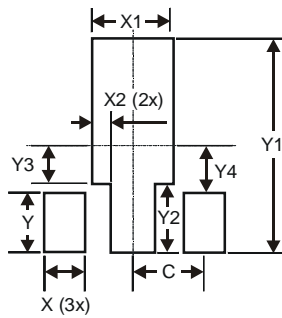
Fig. 11 Gate Charge

## Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.43
D	4.40	4.60
D1	1.52	1.83
E	2.29	2.60
e	1.50 Typ	
e1	3.00 Typ	
H	3.94	4.25
L	0.89	1.20
All Dimensions in mm		

## Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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